

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device having an insulated gate type field effect transistor. A gate insulating film, a gate electrode layer having a predetermined area and facing the semiconductor substrate with the gate insulating film being interposed therebetween, an interlayer insulating film, and a wiring layer connected to the gate electrode layer, are formed on a semiconductor substrate in the order recited. A conductive material layer and a resist layer are formed on the wiring layer. The resist layer is patterned to form a resist mask forming a wiring pattern having an antenna ratio of about ten times or more of the predetermined area of the gate electrode layer. At least the conductive material layer is plasma-etched by using the resist mask as an etching mask, and thereafter, the resist mask is removed and the wiring layer is plasma-etched.